



Organic Memristor Based on the Composite Materials: Conducting and Ionic Polymers, Gold Nanoparticles and Graphenes



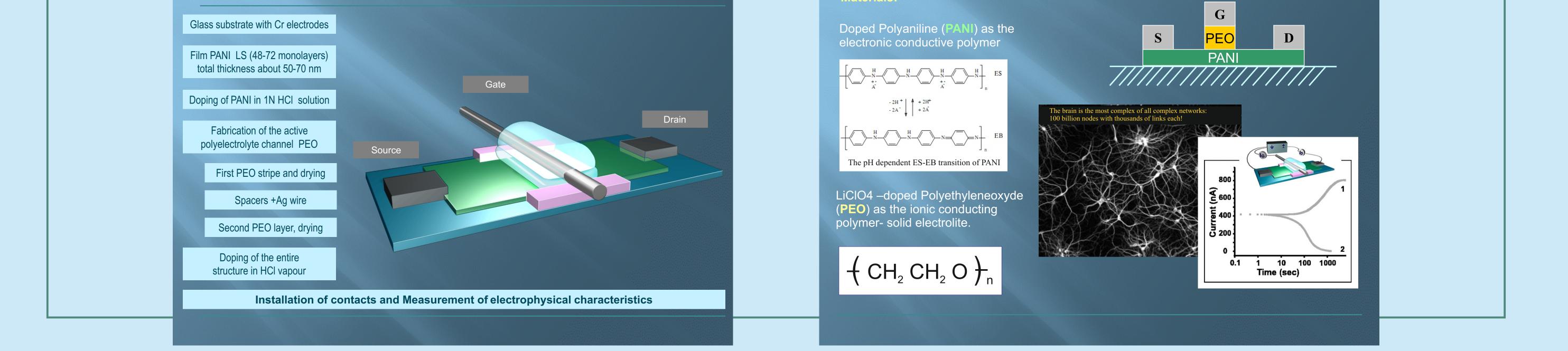
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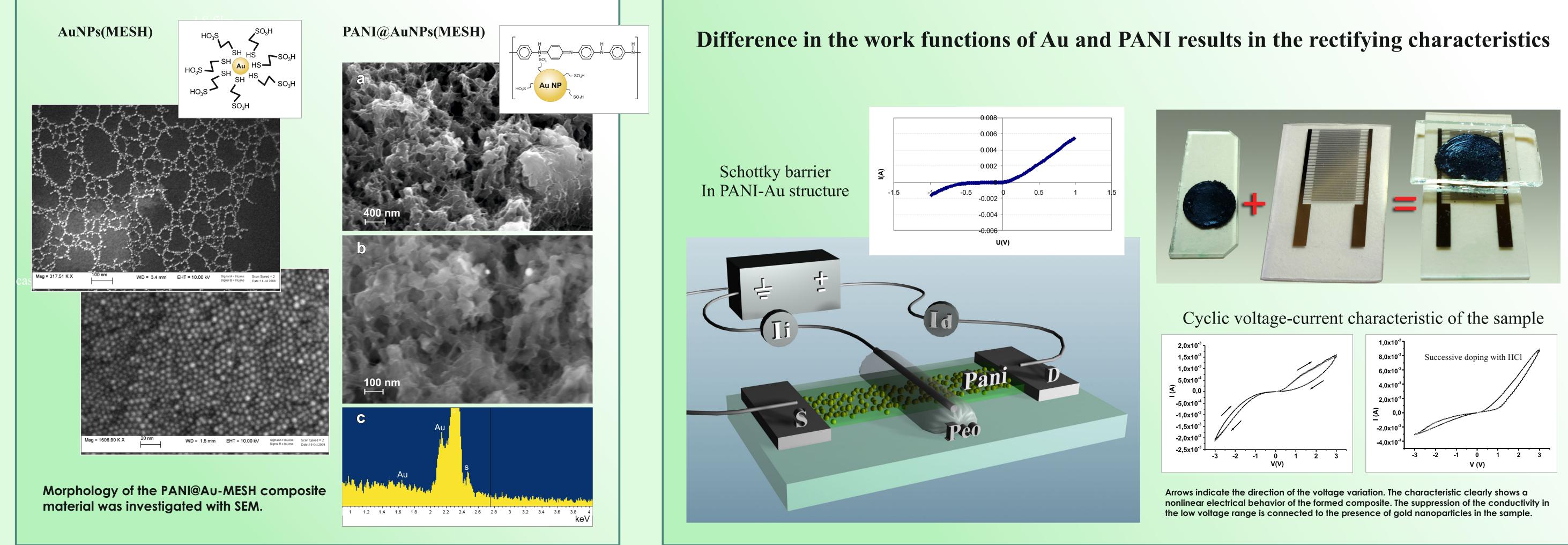
Organic memristor [1] is a solid state device whose electronic conductivity depends on the ionic current that has passed through it. This property is rather similar to the feature of biological synapses and allows to consider the device as a key element for the circuits capable of Hebbian type of learning [2]. The working principle is based on the reversible transfer of the conductivity of the active layer (channel) from good conductor to practically insulator by electrochemical modification of its redox state. This is achieved by depositing a solid electrolyte over the channel, using it as the medium for the electrochemical conductivity variations. Application of the positive voltage higher than the oxidation potential results in the increase of the memristor conductivity, while the application of any negative potential (reduction potential of PANI is about +0.1 V) results in the increase of its resistance.

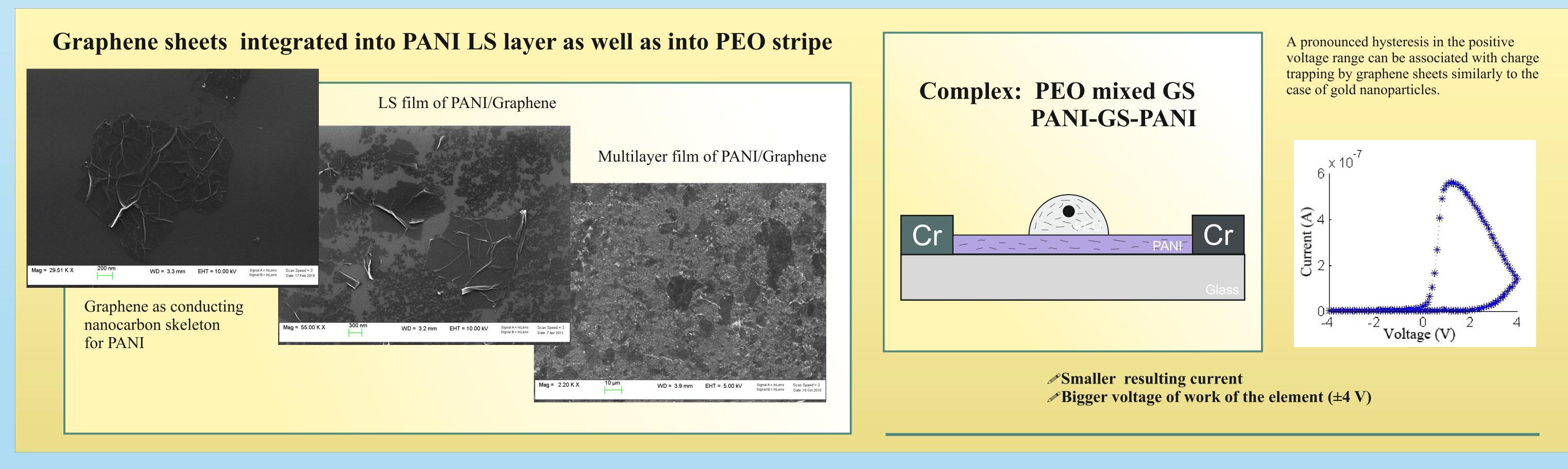
> Step by step manufacturing scheme of polymeric electrochemical element

ELECTROCHEMICAL NONLINEAR ELEMENT



We need another nonlinear element, acting similarly to the body of the neuron, namely, providing a threshold for further signal propagation ("firing"). Such an element can be based on the AuNPs, directly connected to the PANI chain: the difference of the work functions of gold and PANI will provide a Schottky barrier, which while allowing the incoming currents, will block output until the signal overcomes the barrier, in analogy with real neurons.





[1]Erokhin, V., Berzina, T., and Fontana, M.P. 2005. Hybrid electronic device based on polyaniline-polyethylene oxide junction. J. Appl. Phys. 97, 064501.

[2] Hebb, D.O. 1949. The organization of Behavior: a neuropsychological theory. Wiley and Sons, New York.

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